ΡΛΝ	JIT
	SEMI
	CONDUCTOR

TO-252AA

Gate <sup>①</sup>

Drain

Source

# PJD9P06A-AU

### 60V P-Channel Enhancement Mode MOSFET

Voltage

### -60 V Current

### Features

- $R_{DS(ON)}$ ,  $V_{GS}$ @-10V, $I_D$ @-3.5A<170m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @-4.5V, $I_D$ @-2A<220m $\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

### **Mechanical Data**

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams

## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

-7 A

PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-60	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-7.0	А	
	T <sub>C</sub> =100°C		-4.3		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-28		
Power Dissipation	T <sub>C</sub> =25°C	Po	15.6	W	
	T <sub>C</sub> =100°C		6.2		
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	-2.5	А	
	T <sub>A</sub> =70°C		-2.0	А	
Power Dissipation	T <sub>A</sub> =25°C	D	2.0	14/	
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3	W	
Single Pulse Avalanche Energy	(Note 6)	E <sub>AS</sub>	32	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ extsf{ heta}JC}$	8	°C/W	
	Junction to Ambient	$R_{\thetaJA}$	62.5		

Limited only By Maximum Junction Temperature



# PJD9P06A-AU

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		·				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}=0V,I_{D}=-250uA$	-60	-	-	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1.0	-1.88	-2.5	V
	_	V <sub>GS</sub> =-10V,I <sub>D</sub> =-3.5A	-	150	170	mΩ
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}$ =-4.5V,I <sub>D</sub> =-2A	-	190	220	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-60V, $V_{GS}$ =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)		·				
Total Gate Charge	Qg	V <sub>DS</sub> =-30V, I <sub>D</sub> =-3A, V <sub>GS</sub> =-10V <sup>(Note 2,3)</sup>	-	8.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.8	-	
Gate-Drain Charge	$Q_{gd}$		-	1.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1.0MHZ	-	430	-	pF
Output Capacitance	Coss		-	33	-	
Reverse Transfer Capacitance	Crss		-	29	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =-30V, $I_{D}$ =-1.0A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 2,3)	-	5.1	-	
Turn-On Rise Time	t <sub>r</sub>		-	20	-	-
Turn-Off Delay Time	td <sub>(off)</sub>		-	36	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	11	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	Is		-	-	-7	А
Diode Forward Current						
Reverse Recovery Time	V <sub>SD</sub>	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V	-	-0.76	-1.0	V

NOTES :

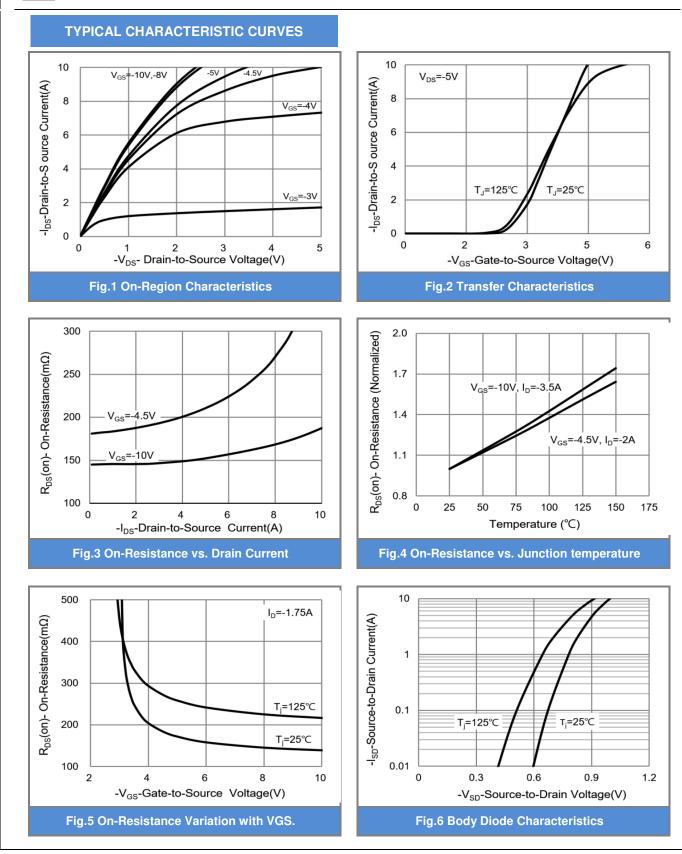
- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
- 6. L=1mH, I\_{AS}=-8A, V\_{GS}=-10V, V\_{DS}=-25V, R\_{G}=25 \text{ ohm}
- 7. Guaranteed by design, not subject to production testing.

SEMI CONDUCTOR

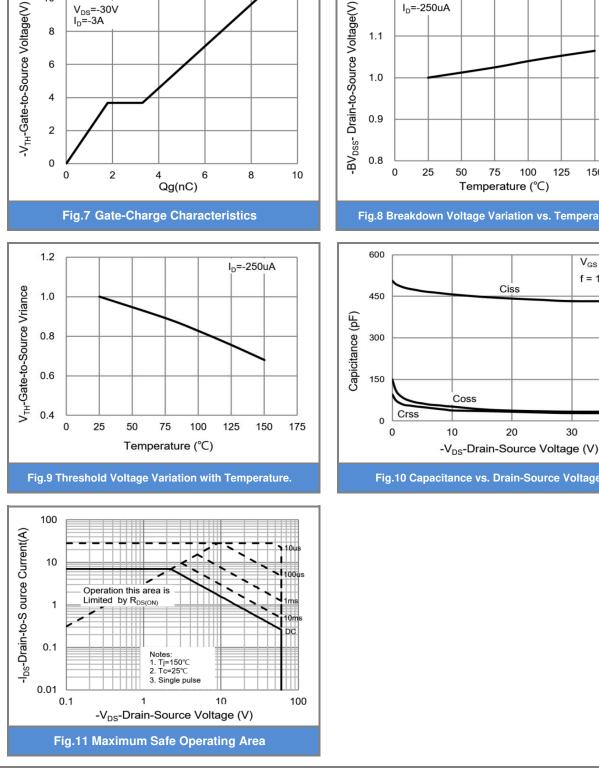
PANJI



## PJD9P06A-AU



June 20,2019-REV.00



1.2

1.1

I<sub>D</sub>=-250uA

# **TYPICAL CHARACTERISTIC CURVES**

### CONDUCTOR

PJD9P06A-AU

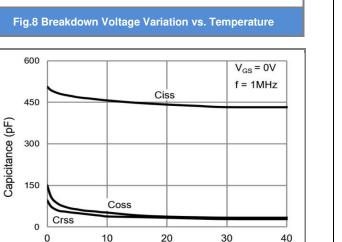
V<sub>DS</sub>=-30V I<sub>D</sub>=-3A



10

8





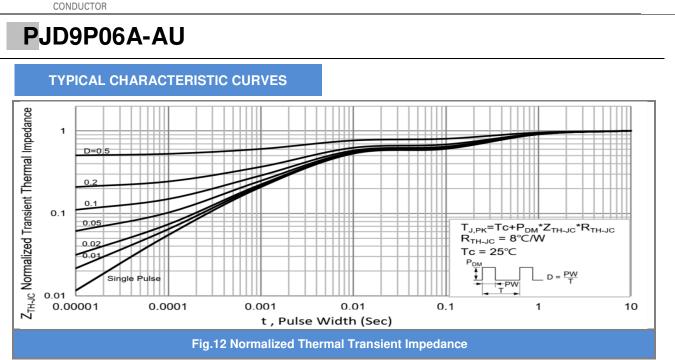
125

175

150

Fig.10 Capacitance vs. Drain-Source Voltage.





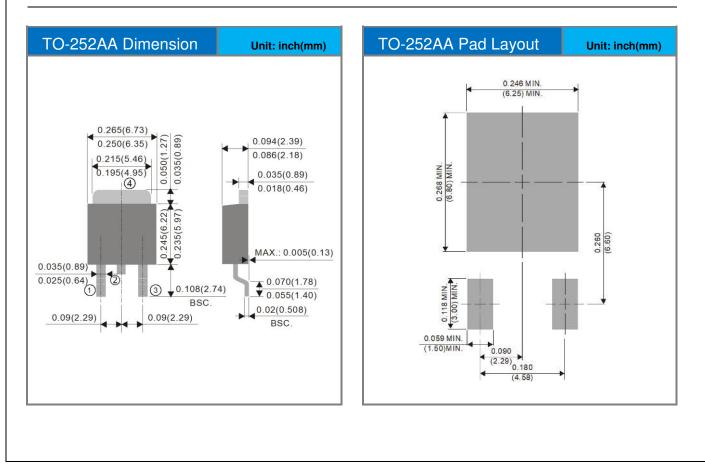


# PJD9P06A-AU

### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD9P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D9P06A	Halogen free

### **Packaging Information & Mounting Pad Layout**





# PJD9P06A-AU

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